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Triacs

Silicon Bidirectional Thyristors

Designed for high performance full-wave AC control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 15 Amperes RMS at 80°C
- Uniform Gate Trigger Currents in Three Modes
- High Immunity to dv/dt 250 V/us minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220 Package
- High Commutating di/dt 9.0 A/ms minimum at 125°C
- Operational in Three Quadrants, Q1, Q2, and Q3
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (-40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC15M MAC15N	V _{DRM,} V _{RRM}	600 800	V
On–State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 80°C)	I _{T(RMS)}	15	Α
Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 125°C)	I _{TSM}	150	A
Circuit Fusing Consideration (t = 8.3 ms)	I ² t	93	A ² s
Peak Gate Power (Pulse Width \leq 1.0 μ s, T _C = 80°C)	P _{GM}	20	W
Average Gate Power (t = 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	W
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

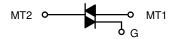
 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor®

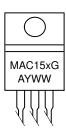
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TRIACS 15 AMPERES RMS 600 thru 800 VOLTS





MARKING DIAGRAM



TO-220 CASE 221A STYLE 4

= M or N

A = Assembly Location

/ = Year

NW = Work Week

G = Pb-Free Package

PIN ASSIGNMENT			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	Main Terminal 2		

ORDERING INFORMATION

Device	Package	Shipping
MAC15MG	TO-220 (Pb-Free)	50 Units / Rail
MAC15NG	TO-220 (Pb-Free)	50 Units / Rail

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ hetaJC}$ $R_{ hetaJA}$	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T _L	260	°C

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted; Electricals apply in both directions)

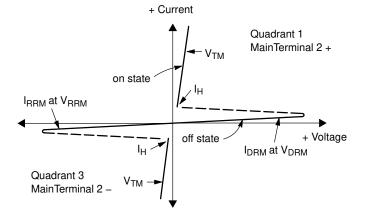
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Blocking Current (V _D = Rated V _{DRM} , V _{RRM} ; Gate Open)	$T_J = 25$ °C $T_J = 125$ °C	I _{DRM} , I _{RRM}	_ _	_ _	0.01 2.0	mA
ON CHARACTERISTICS		•	•	•	•	•
Peak On-State Voltage (Note 2) (I _{TM} = ±21 A Peak)		V _{TM}	-	1.2	1.6	٧
Gate Trigger Current (Continuous DC) (V_D = 12 V, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		I _{GT}	5.0 5.0 5.0	13 16 18	35 35 35	mA
Hold Current ($V_D = 12 \text{ Vdc}$, Gate Open, Initiating Current = $\pm 150 \text{ mA}$)		I _H	-	20	40	mA
Latching Current (V_D = 24 V, I_G = 35 mA) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		IL	- - -	33 36 33	50 80 50	mA
Gate Trigger Voltage (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-)		V _{GT}	0.5 0.5 0.5	0.75 0.72 0.82	1.5 1.5 1.5	V
DYNAMIC CHARACTERISTICS						
Rate of Change of Commutating Current; See Figure 10. $(V_D=400~V,~I_{TM}=6.0~A,~Commutating~dv/dt=24~V/\mu s,~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_L=10~C_$	1	(di/dt) _c	9.0	-	-	A/ms
Critical Rate of Rise of Off-State Voltage $(V_D = Rated\ V_{DRM},\ Exponential\ Waveform,\ Gate\ Open,\ T_J = 125^{\circ}C)$		dv/dt	250	-	_	V/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

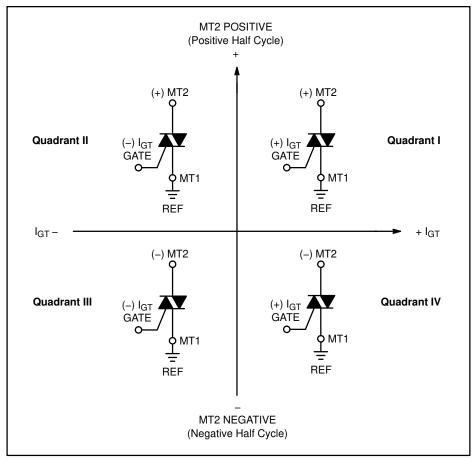
2. Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

 $\dot{\text{With}}$ in–phase signals (using standard AC lines) quadrants I and III are used.

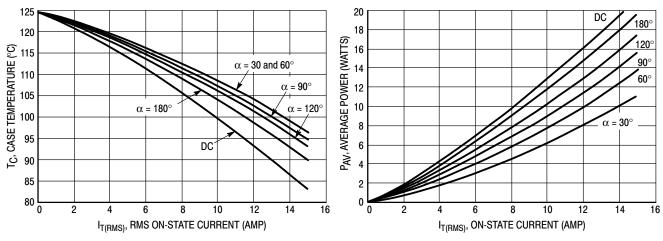
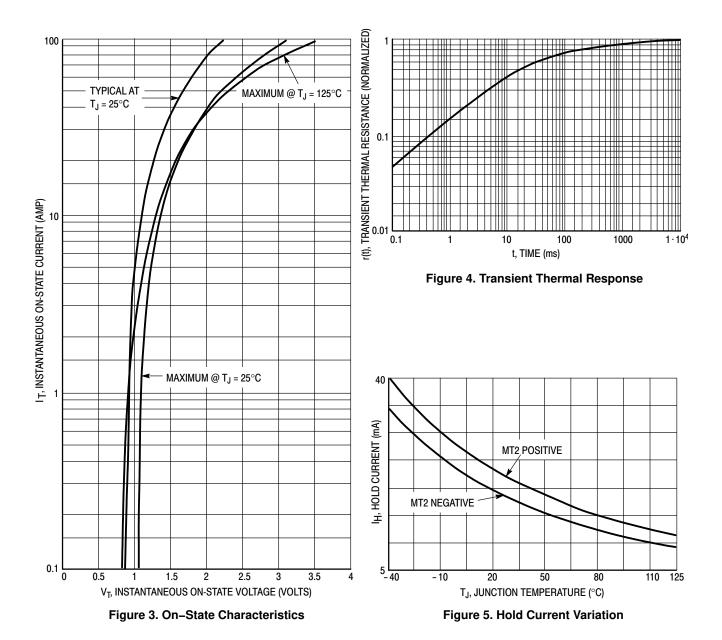


Figure 1. RMS Current Derating

Figure 2. On-State Power Dissipation



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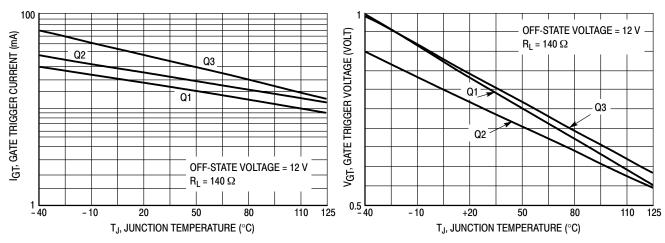


Figure 6. Typical Holding Current versus Junction **Temperature**

Figure 7. Gate Trigger Voltage versus Junction **Temperature**

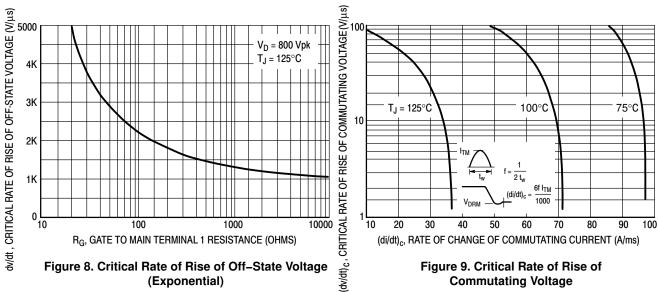
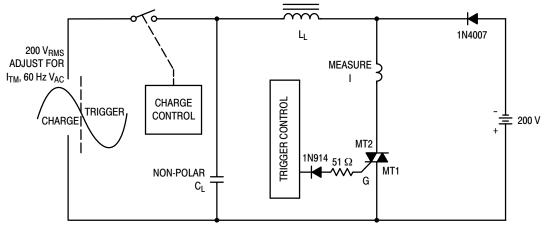


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential)

Figure 9. Critical Rate of Rise of **Commutating Voltage**

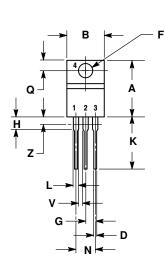


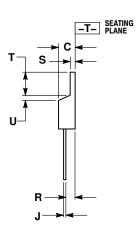
Note: Component values are for verification of rated (di/dt)_c. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)c

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 4: PIN 1. MAIN TERMINAL 1

- 2. MAIN TERMINAL 2
- 3. GATE
- MAIN TERMINAL 2

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